MOSFETs Silicon N-channel MOS (U-MOSⅧ-H)

TPH2R306NH

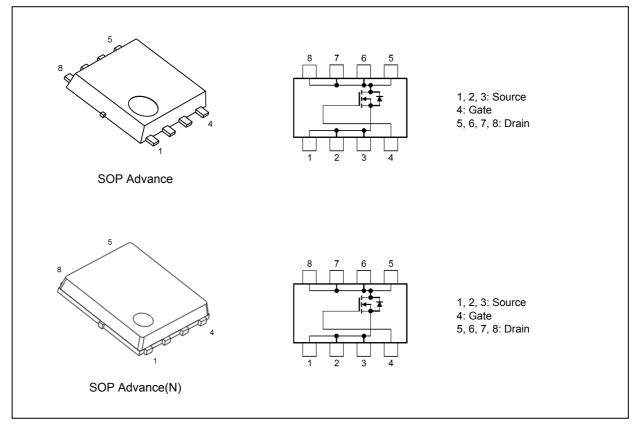
1. Applications

- DC-DC Converters
- Switching Voltage Regulators
- Motor Drivers

2. Features

- (1) High-speed switching
- (2) Small gate charge: $Q_{SW} = 26 \text{ nC}$ (typ.)
- (3) Low drain-source on-resistance: $R_{DS(ON)} = 1.9 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (4) Low leakage current: $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 60 \ V)$
- (5) Enhancement mode: V_{th} = 2.0 to 4.0 V (V_{DS} = 10 V, I_D = 1.0 mA)

3. Packaging and Internal Circuit



The package can be selected according to your preference. For details, please contact your TOSHIBA sales representative.

4. Absolute Maximum Ratings (Note) ($T_a = 25^{\circ}C$ unless otherwise specified)

Characterist	ics		Symbol	Rating	Unit
Drain-source voltage			V _{DSS}	60	V
Gate-source voltage			V _{GSS}	±20	
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	I _D	130	A
Drain current (DC)	(T _c = 25°C)	(Note 1)	Ι _D	60	
Drain current (pulsed)	(t = 1 ms)	(Note 1)	I _{DP}	200	
Power dissipation	(T _c = 25°C)		PD	78	W
Power dissipation	(t = 10 s)	(Note 3)	PD	2.8	W
Power dissipation	(t = 10 s)	(Note 4)	PD	1.6	W
Single-pulse avalanche energy		(Note 5)	E _{AS}	453	mJ
Avalanche current			I _{AR}	60	A
Channel temperature			T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteris	tics		Symbol	Max	Unit
Channel-to-case thermal resistance	(T _c = 25°C)		R _{th(ch-c)}	1.60	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 3)	R _{th(ch-a)}	44.6	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 4)	R _{th(ch-a)}	78.1	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Limited by silicon chip capability. Package limit is 60 A.

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V_{DD} = 48 V, T_{ch} = 25°C (initial), L = 0.097 mH, I_{AR} = 60 A

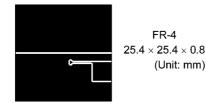
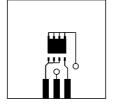


Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)



FR-4 25.4 × 25.4 × 0.8 (Unit: mm)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

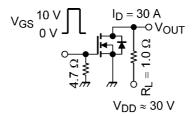
6. Electrical Characteristics

6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V			±0.1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	60	—	—	V
	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	45	_	_	
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 1.0 mA	2.0	_	4.0	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 6.5 V, I _D = 15 A		2.6	4.7	mΩ
		V _{GS} = 10 V, I _D = 30 A		1.9	2.3	

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 30 V, V _{GS} = 0 V, f = 1 MHz		4700	6100	pF
Reverse transfer capacitance	C _{rss}]		55	100	
Output capacitance	C _{oss}]		1500	_	
Gate resistance	rg	—		1.0	1.5	Ω
Switching time (rise time)	t _r	See Figure 6.2.1.		9.9	_	ns
Switching time (turn-on time)	t _{on}]		29	_	
Switching time (fall time)	t _f]		16		
Switching time (turn-off time)	t _{off}]		50	—	



Duty \leq 1%, t_W = 10 μs

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

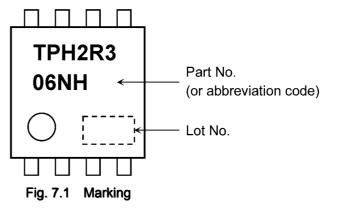
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 30 \text{ V}, \text{ V}_{GS} \text{ = } 10 \text{ V}, \text{ I}_{D} \text{ = } 60 \text{ A}$	—	72	—	nC
Gate-source charge 1	Q _{gs1}		_	25	_	
Gate-drain charge	Q _{gd}		_	17	_	
Gate switch charge	Q _{SW}		_	26	_	

6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

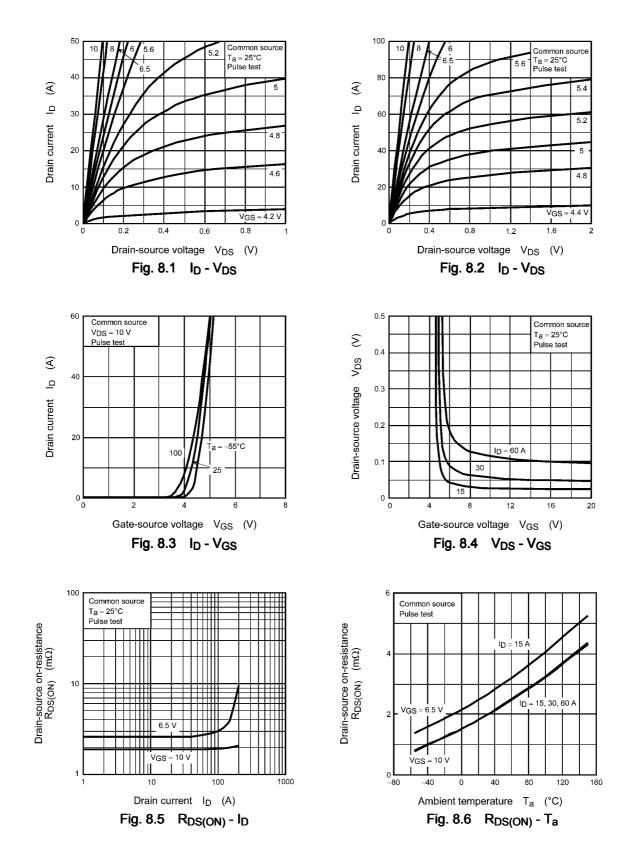
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (No	e 6) I _{DRP}	—	_	—	200	А
Diode forward voltage	V _{DSF}	I _{DR} = 60 A, V _{GS} = 0 V			-1.2	V

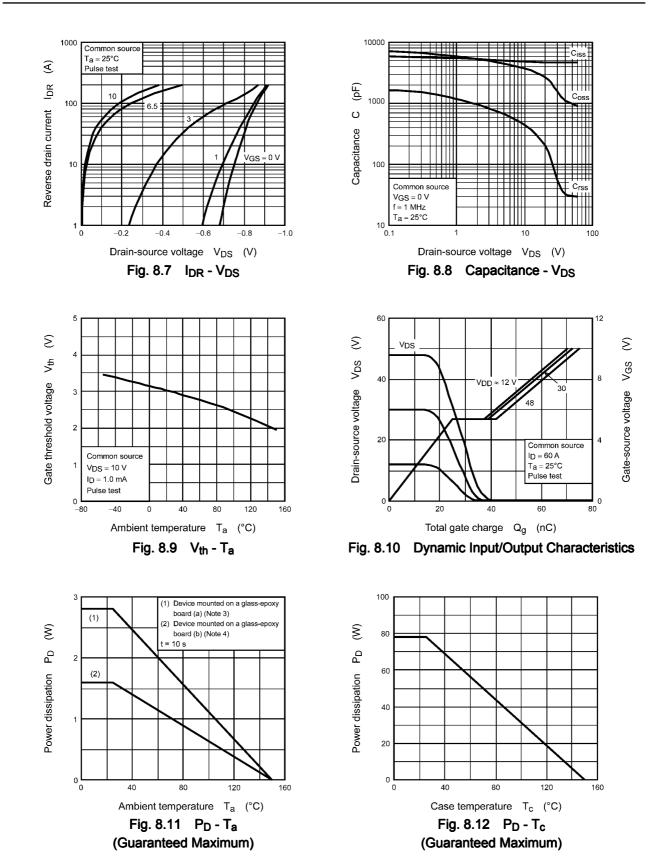
Note 6: Ensure that the channel temperature does not exceed 150°C.

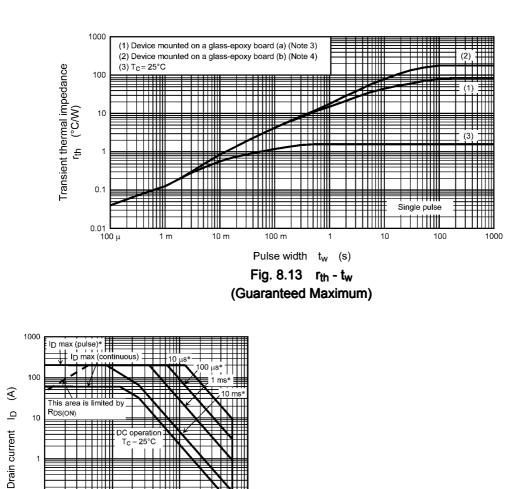
7. Marking



8. Characteristics Curves (Note)







Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

0.1

0.01 L 0.1

* Single pulse

Curves must be derated lin with increase in temperature.

 $T_a = 25^{\circ}C$

Drain-source voltage V_{DS} (V) Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

VDSS ma

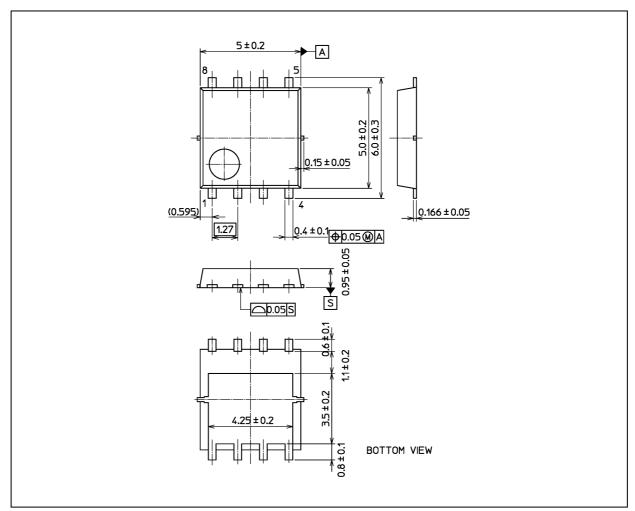
10

100

TPH2R306NH

Package Dimensions

Unit: mm



The package can be selected according to your preference. For details, please contact your TOSHIBA sales representative.

Weight: 0.087 g (typ.)

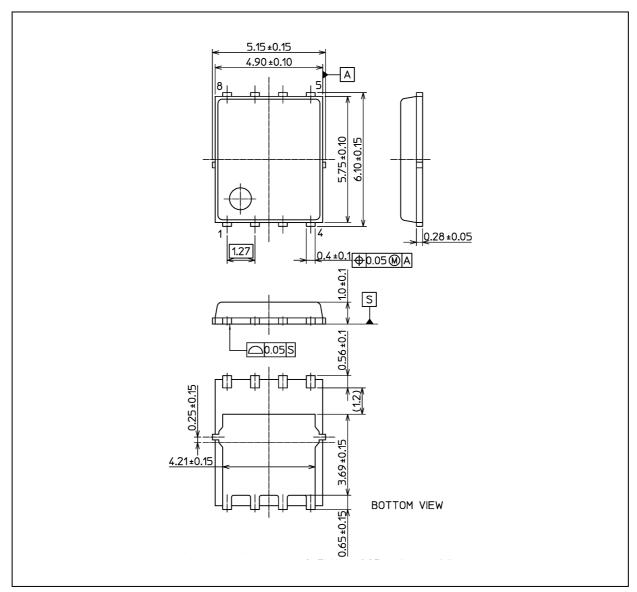
	Package Name(s)
TOSHIBA: 2-5Q1S	
Nickname: SOP Advance	



TPH2R306NH

Package Dimensions

Unit: mm



The package can be selected according to your preference. For details, please contact your TOSHIBA sales representative.

Weight: 0.111 g (typ.)

Package Name(s)			
TOSHIBA: 2-5W1A			
Nickname: SOP Advance(N)			

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